

/ Descriptions

TO-220FL N MOS N-CHANNEL MOSFET in a TO-220FL Plastic Package.

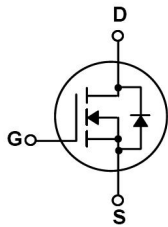
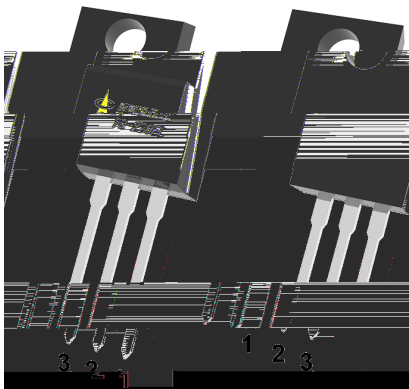
/ Features

Low gate charge, Low Crss , Fast switching.

/ Applications

UPS

High efficiency switch mode power supplies, Electronic lamp ballasts based on half bridge, UPS .

/ Equivalent Circuit**/ Pinning**

PIN1 G

PIN 2 D

PIN 3 S

/ Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	650	V
Drain Current	$I_D(T_c=25^\circ\text{C})$	20	A
Drain Current - Pulsed	I_{DM}	40	A
Gate-Source Voltage	V_{GS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	477	mJ
Avalanche Current	I_{AR}	10.5	A
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.27	/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	/W
Power Dissipation	P_D	55	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	

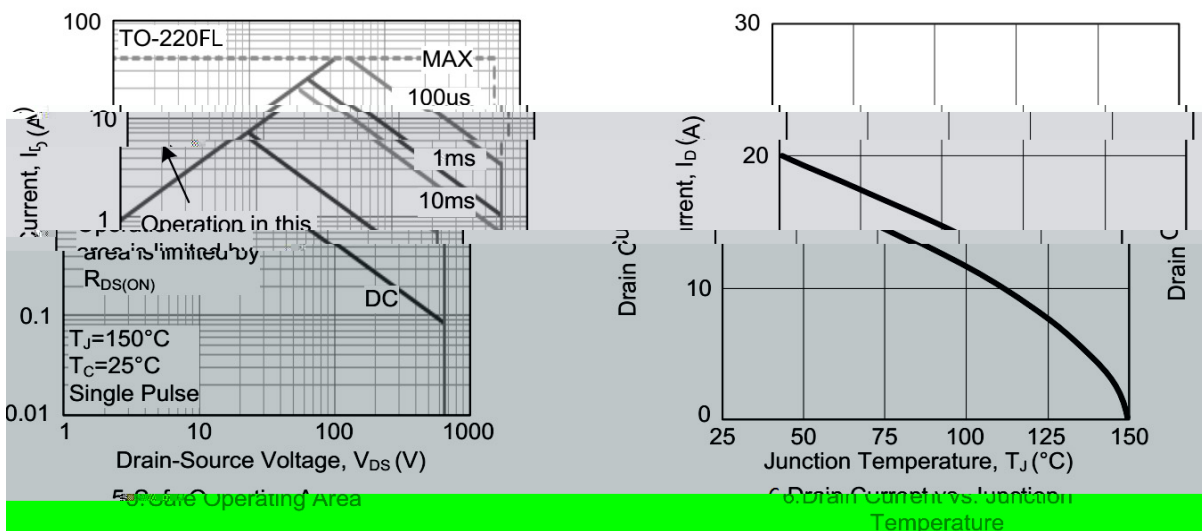
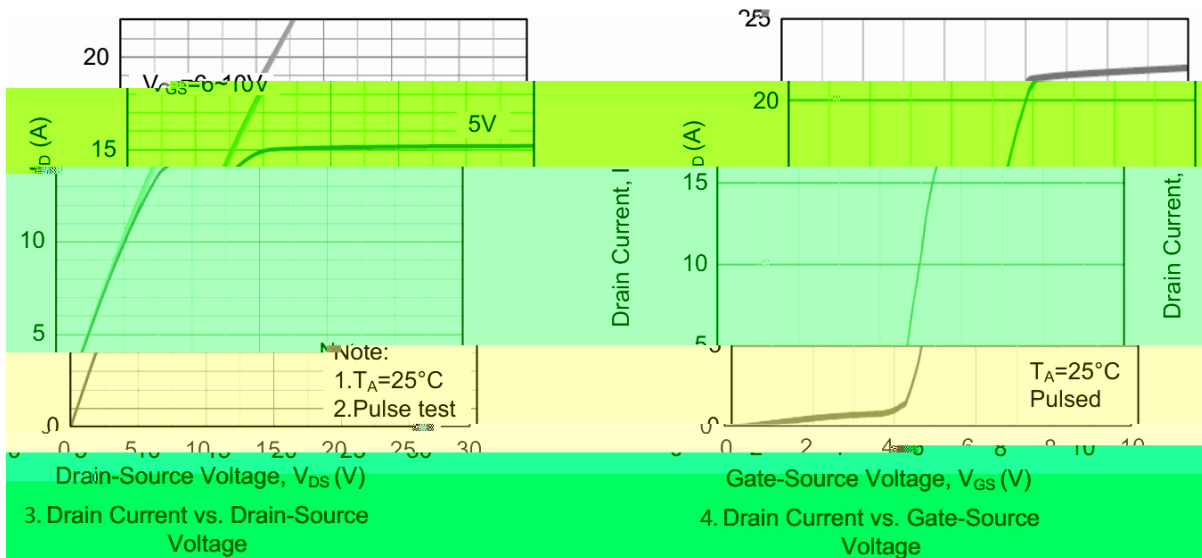
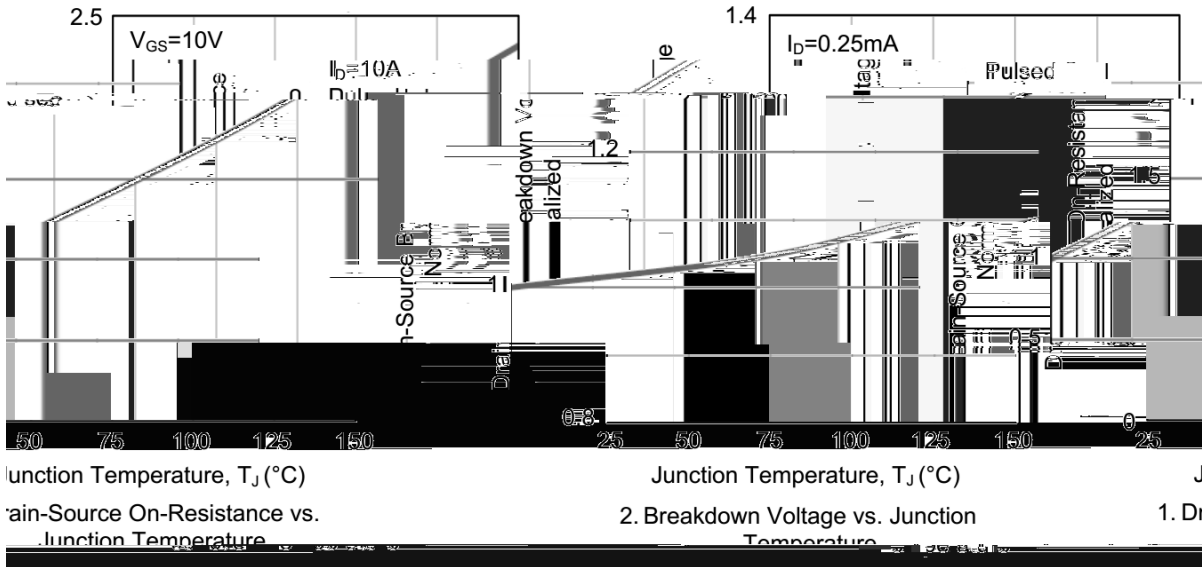
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS}=0V$ $I_D=250\mu A$	650			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=650V$ $V_{GS}=0V$			1.0	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 30V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2.0	3.2	4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=10A$		0.42	0.55	Ω
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=20A$			1.4	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		3400		pF
Output Capacitance	C_{oss}			270		pF
Reverse Transfer Capacitance	C_{rss}			23		pF
Total Gate Charge	Q_G	$V_{DS}=100V$ $I_D=20A$ $V_{GS}=10V$		54		nC
Gate-Source Charge	Q_{GS}			10		ns
Gate-Drain Charge	Q_{GD}			13		ns

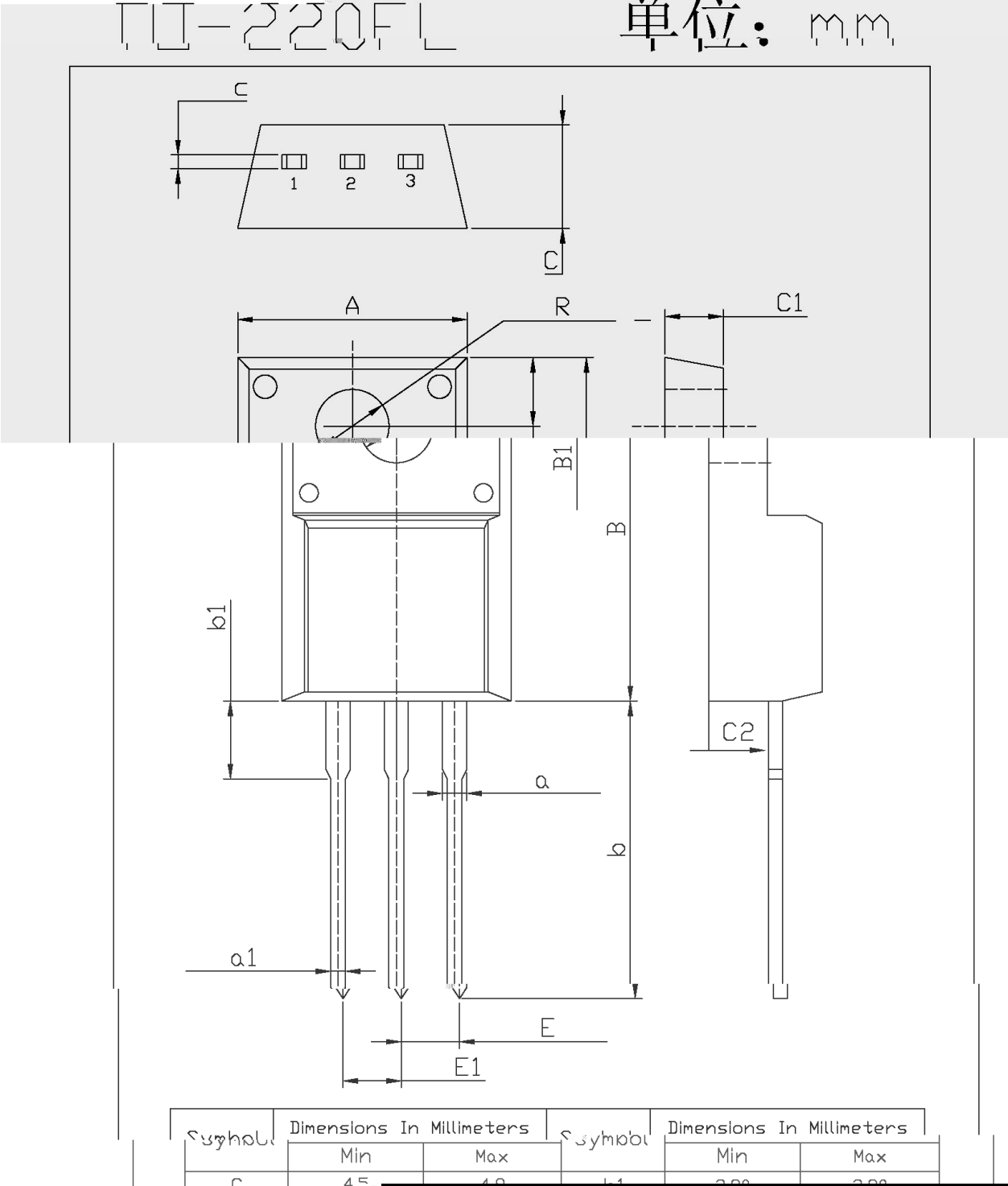
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=100V$ $I_D=20A$ $V_{GS}=10V$ $R_G=25\Omega$		28		ns
Turn-On Rise Time	t_r			35		
Turn-Off Delay Time	$t_{d(off)}$			140		
Turn-Off Fall Time	t_f			76		
Maximum Continuous Drain-Source Diode Forward Current	I_S				20	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				40	A
Reverse Recovery Time	t_{rr}	$V_{GS} = 0V$ $I_S = 20A$ $dI_F/dt = 100 A/\mu s$		506		ns
Reverse Recovery Charge	Q_{rr}			9		μC

/ Electrical Characteristic Curve



/ Package Dimensions





/ Marking Instructions



BR

20N65

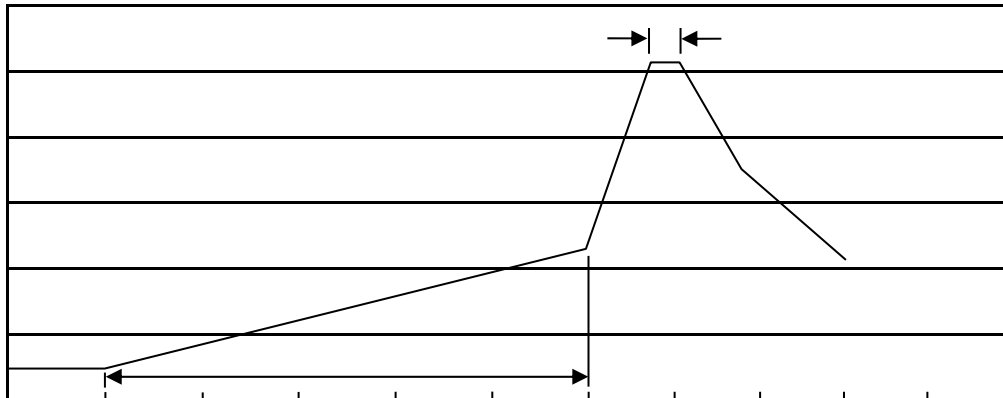
Note:

BR: Company Code

20N65: Product Type Code

****: Lot No. Code, code change with Lot No

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | |
|---|------------|-----------|---|
| 1 | 25 150 | 60 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | 5±0.5sec; | 2.Peak Temp.:255±5 , Duration:5±0.5sec. |
| 3 | 2 10 /sec. | | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ TUBE

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box
TO-220FL	50	20	1,000	5	5,000	532×33×7.0	555×164×50	575×290×180

/ Notices